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Data Sheet

October 2013

N-Channel Logic Level Power MOSFET 50 V, 14 A, 100 $m\Omega$

These are N-channel power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers and relay drivers. This performance is accomplished through a special gate oxide design which provides full rated conductance at gate bias in the 3V-5V range, thereby facilitating true on-off power control directly from logic level (5V) integrated circuits.

Formerly developmental type TA09870.

Ordering Information

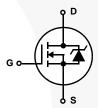
PART NUMBER	PACKAGE	BRAND
RFD14N05L	TO-251AA	14N05L
RFD14N05LSM	TO-252AA	14N05L
RFD14N05LSM9A	TO-252AA	14N05L

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252AA variant in the tape and reel, i.e., RFD14N05LSM9A.

Features

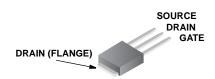
- 14A, 50V
- $r_{DS(ON)} = 0.100\Omega$
- Temperature Compensating PSPICE[®] Model
- Can be Driven Directly from CMOS, NMOS, and TTL Circuits
- · Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175°C Operating Temperature
- · Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging

JEDEC TO-251AA



JEDEC TO-252AA



RFD14N05L, RFD14N05LSM

Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

	RFD14N05L, RFD14N05LSM,	
	RFD14N05LSM9A	UNITS
Drain to Source Voltage (Note 1)V _{DSS}	50	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	50	V
Gate to Source Voltage	±10	V
Continuous Drain Current	14	Α
Pulsed Drain Current (Note 3)	Refer to Peak Current Curve	
Pulsed Avalanche RatingE _{AS}	Refer to UIS Curve	
Power Dissipation	48	W
Derate above 25°C	0.32	W/oC
Operating and Storage Temperature	-55 to 175	oC
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	oC
Package Body for 10s, See Techbrief 334	260	οС

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}C$ to $150^{\circ}C$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CO	ONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V, Figure 13		50	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, $I_D = 250\mu$ A, Figure12		1	-	2	V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 40V, V_{GS} = 0V$	J	-	-	1	μА
		$V_{DS} = 40V, V_{GS} = 0V, T_{C} = 150^{\circ}C$		-	-	50	μΑ
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 10V$		-	-	±100	nA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	$I_D = 14A, V_{GS} = 5V,$	Figures 9, 11	-	-	0.100	Ω
Turn-On Time	t _(ON)	$V_{DD} = 25V, I_{D} = 7A,$ $R_{L} = 3.57\Omega, V_{GS} = 5V,$ $R_{GS} = 0.6\Omega$		-	-	60	ns
Turn-On Delay Time	t _{d(ON)}			-	13	-	ns
Rise Time	t _r			-	24	-	ns
Turn-Off Delay Time	t _d (OFF)			-	42	-	ns
Fall Time	t _f			-	16	-	ns
Turn-Off Time	t _(OFF)			-	-	100	ns
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 10V	$V_{DD} = 40V, I_D = 14A,$	-	-	40	nC
Gate Charge at 5V	Q _{g(5)}	$V_{GS} = 0V \text{ to } 5V$ $R_L = 2.86\Omega$	-	-	25	nC	
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 1V Figures 20, 21		-	-	1.5	nC
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz Figure 14		-	670	-	pF
Output Capacitance	Coss			-	185	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	50	-	pF
Thermal Resistance Junction to Case R _θ JC				-)	-	3.125	oC/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-251		-	- /	100	°C/W
R		TO-252		-	- 1	100	°C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	I _{SD} = 14A	-	-	1.5	V
Diode Reverse Recovery Time	t _{rr}	$I_{SD} = 14A$, $dI_{SD}/dt = 100A/\mu s$	-	-	125	ns

NOTES:

- 2. Pulse Test: Pulse Width ≤300ms, Duty Cycle ≤2%.
- 3. Repetitive Rating: Pulse Width limited by max junction temperature. See Transient Thermal Impedance Curve (Figure 3) and Peak Current Capability Curve (Figure 5).

Typical Performance Curves Unless Otherwise Specified

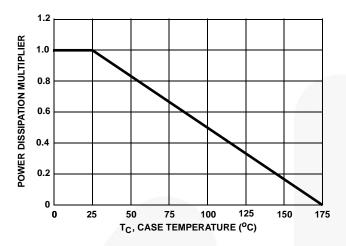


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs
TEMPERATURE

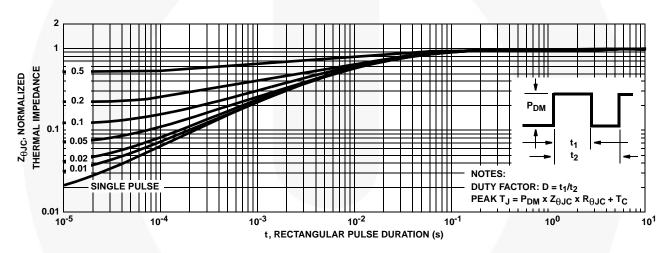
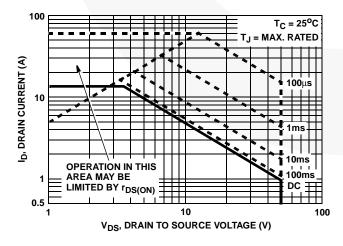


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

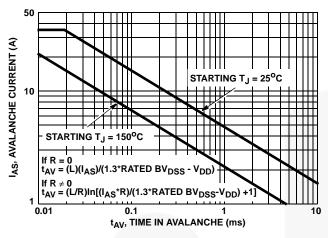


200 TRANSCONDUCTANCE MAY LIMIT CURRENT IN THIS REGION FOR TEMPERATURES ABOVE 25°C DERATE PEAK € IDM, PEAK CURRENT CAPABILITY **CURRENT AS FOLLOWS:** 100 $V_{GS} = 5V$ = 25°C 10 10⁻⁵ 10⁻⁴ 10⁻² 10⁻¹ 10⁰ 10¹ t, PULSE WIDTH (s)

FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

FIGURE 5. PEAK CURRENT CAPABILITY

Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

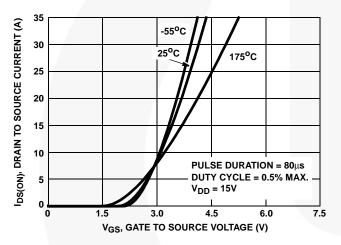


FIGURE 8. TRANSFER CHARACTERISTICS

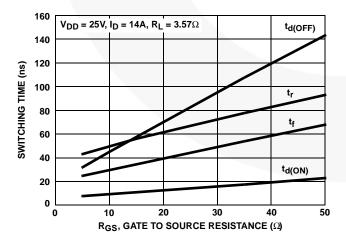


FIGURE 10. SWITCHING TIME vs GATE RESISTANCE

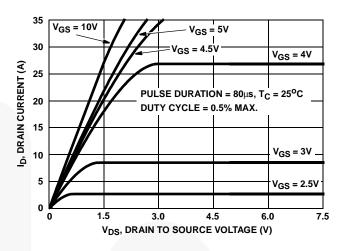


FIGURE 7. SATURATION CHARACTERISTICS

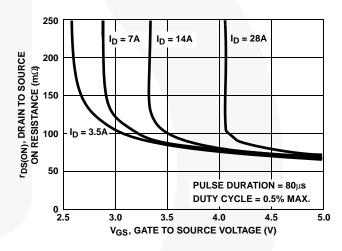


FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

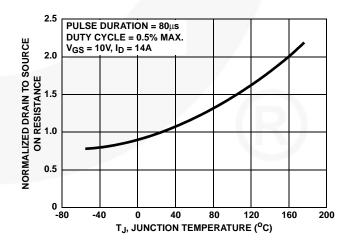


FIGURE 11. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

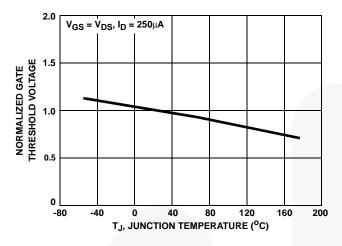


FIGURE 12. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

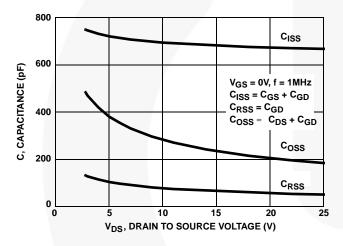


FIGURE 14. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

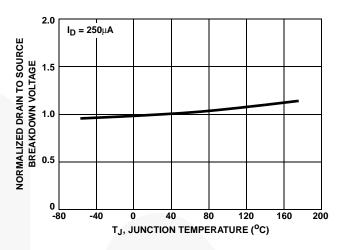
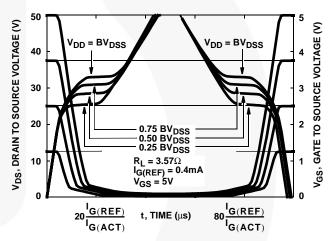


FIGURE 13. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260, FIGURE 15. TRANSCONDUCTANCE vs DRAIN CURRENT

Test Circuits and Waveforms

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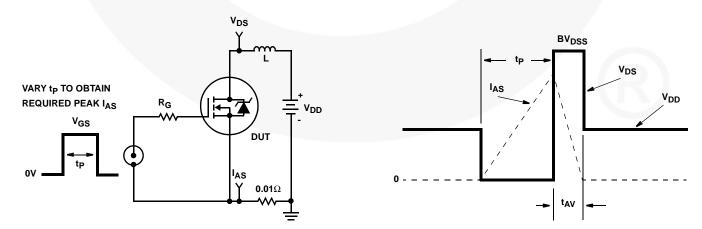


FIGURE 16. UNCLAMPED ENERGY TEST CIRCUIT FIGURE 17. UNCLAMPED ENERGY WAVEFORMS

Test Circuits and Waveforms (Continued)

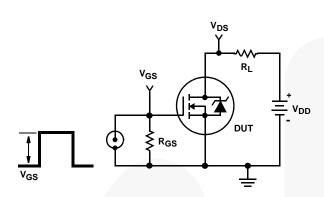


FIGURE 18. SWITCHING TIME TEST CIRCUIT

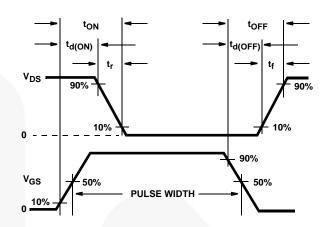


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

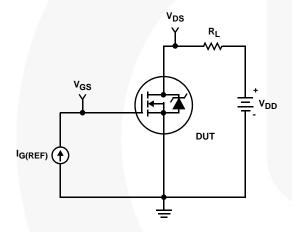


FIGURE 20. GATE CHARGE TEST CIRCUIT

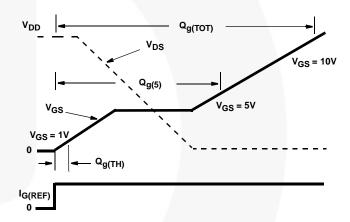


FIGURE 21. GATE CHARGE WAVEFORMS

PSPICE Electrical Model

.ENDS

```
.SUBCKT_RFP14N05L_2 1 3:
                                 rev 9/15/94
CA 12 8 1.464e-9
CB 15 14 1.64e-9
                                                                    DPLCAP
CIN 6 8 6.17e-10
                                                                                                                  DRAIN
                                                             10
                                                                                                         LDRAIN
DBODY 7 5 DBDMOD
DBREAK 5 11 DBKMOD
                                                                                 RSCL1
DPLCAP 10 5 DPLCAPMOD
                                                                                         DBREAK
                                                                  RSCL2
                                                                                  ESCL
EBREAK 11 7 17 18 65.35
EDS 14 8 5 8 1
                                                                                50
EGS 13 8 6 8 1
                                                                                                          DBODY
                                                                                RDRAIN
                                                         ESG
ESG 6 10 6 8 1
                                                                                         EBREAK (17)
                                                                      VTO +
EVTO 20 6 18 8 1
                                                                                         MOS<sub>2</sub>
                                                        EVTO
                                   GATE
IT 8 17 1
                                                      20
                                                                                MOS<sub>1</sub>
                                          LGATE RGATE
LDRAIN 2 5 1e-9
                                                                 RIN
                                                                          CIN
LGATE 1 9 5.68e-9
                                                                                                        LSOURCE
                                                                                         RSOURCE
LSOURCE 3 7 5.35e-9
                                                                                   8
                                                                                                               ,_
→ 3
SOURCE
MOS1 16 6 8 8 MOSMOD M = 0.99
MOS2 16 21 8 8 MOSMOD M = 0.01
                                                                  S2A
                                                        S1A
                                                                                                   RBREAK
                                                                 14
                                                            13
                                                                                                            18
RBREAK 17 18 RBKMOD 1
                                                                 13
RDRAIN 50 16 RDSMOD 33.1e-3
                                                        S1B
                                                                    S2B
                                                                                                             RVTO
RGATE 9 20 5.85
RIN 6 8 1e9
                                                                                                             19
                                                        CA
                                                                          CB
                                                                                                ^{(\!\!\!\!)}
                                                                                                    IT
RSCL1 5 51 RSCLMOD 1e-6
                                                                                                             VBAT
RSCL2 5 50 1e3
                                                            EGS
                                                                        EDS
RSOURCE 8 7 RDSMOD 14.3e-3
RVTO 18 19 RVTOMOD 1
S1A 6 12 13 8 S1AMOD
S1B 13 12 13 8 S1BMOD
S2A 6 15 14 13 S2AMOD
S2B 13 15 14 13 S2BMOD
VBAT 8 19 DC 1
VTO 21 6 0.485
ESCL 51 50 VALUE = \{(V(5,51)/ABS(V(5,51)))^*(PWR(V(5,51)^*1e6/46,7))\}
.MODEL DBDMOD D (IS = 2.23e-13 RS = 1.15e-2 TRS1 = 1.64e-3 TRS2 = 7.89e-6 CJO = 6.83e-10 TT = 3.68e-8)
.MODEL DBKMOD D (RS = 3.8e-1 TRS1 = 1.89e-3 TRS2 = 1.13e-5)
.MODEL DPLCAPMOD D (CJO = 25.7e-11 IS = 1e-30 N = 10)
.MODEL MOSMOD NMOS (VTO = 1.935 KP = 18.89 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)
.MODEL RBKMOD RES (TC1 = 7.18e-4 TC2 = 1.53e-6)
.MODEL RDSMOD RES (TC1 = 4.45e-3 TC2 = 2.9e-5)
.MODEL RSCLMOD RES (TC1 = 2.8e-3 TC2 = 6.0e-6)
.MODEL RVTOMOD RES (TC1 = -1.7e-3 TC2 = -2.0e-6)
.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -3.55 VOFF= -1.55)
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -1.55 VOFF= -3.55)
.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -2.55 VOFF= 2.45)
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 2.45 VOFF= -2.55)
```

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-circuit for the Power MOSFET Featuring Global Temperature Options**; authored by William J. Hepp and C. Frank Wheatley.



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